



SPDT Switch for 3G/4G Applications

Description

The MXD8626C is a Single-Pole, Double-Throw (SPDT) LTE/WCDMA switch. Switching is controlled by a GPIO interface with a single control pin.

The MXD8626C is provided in a compact 1.1mm x 0.7mm x 0.45mm 6-lead DFN package, which meets the requirements for board-level assembly. No external DC blocking capacitors are required as long as no DC voltage is applied on any RF path. A functional block diagram and the pin configuration are shown in Figure 1.

Applications

- GSM/WCDMA/LTE

Features

- Broadband frequency range: 0.4 to 3.0GHz
- Low insertion loss: 0.35dB @2.7GHz
- High isolation: 25dB @2.7GHz
- High Input 0.1dB compression point: 35dBm
- Single GPIO control line with VDD voltage regulator:
 - $V_{DD} = 2.5$ to $3.0V$
 - $V_{CTL_H} = 1.5$ to $3.0V$
- Compact, 6-Lead DFN, 400um pitch (1.1mm x 0.7mm x 0.45mm) package, MSL1

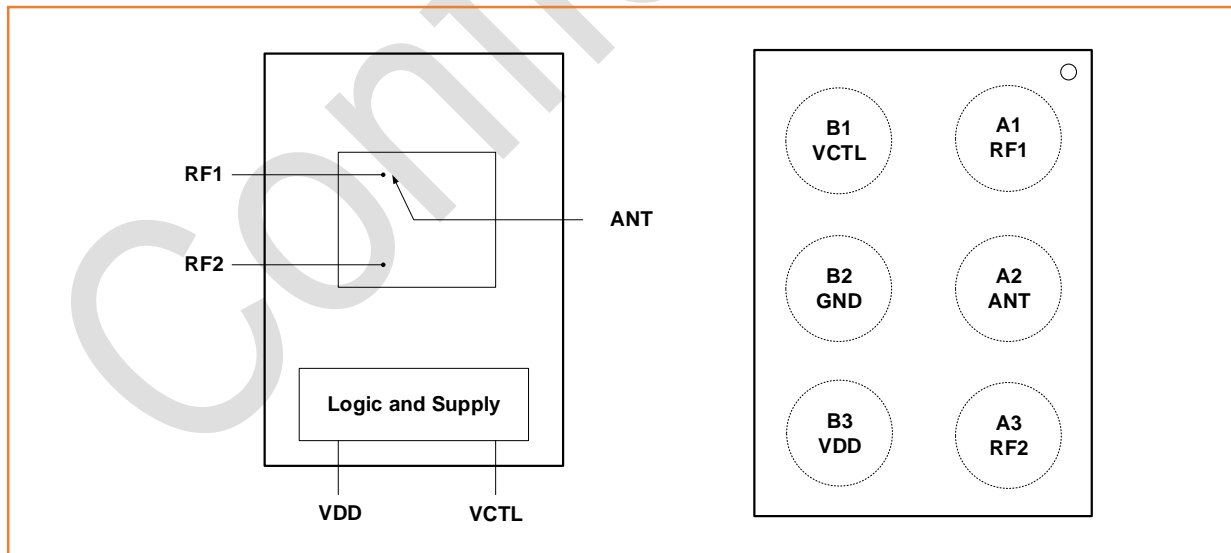


Figure 1 Functional Block and Pin Out(Top View)

Function Characteristics

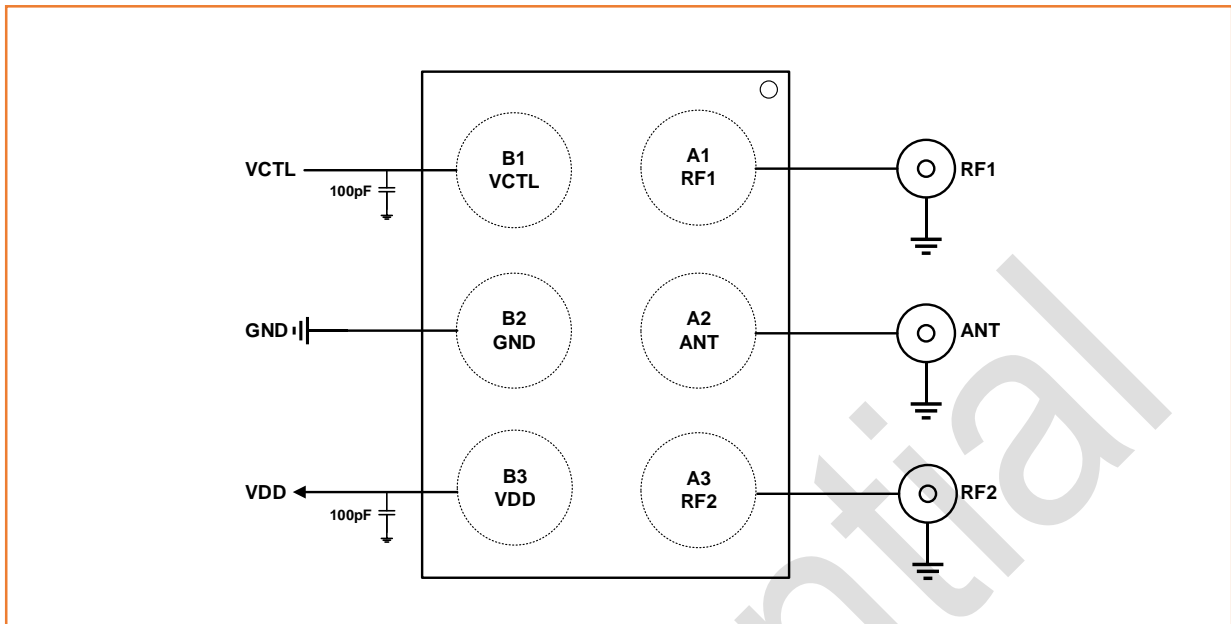


Figure 2 Application Circuit

Table 1 Pin Descriptions

NO.	Name	Description	NO.	Name	Description
A1	RF1	RF Port1	B1	VCTL	Logic Control Voltage
A2	ANT	Antenna Port	B2	GND	Ground
A3	RF2	RF Port2	B3	VDD	DC Supply Voltage

Table 2 VCTL Truth Table for RF Channel Operating Modes

VCTL	RF Channel Operating Mode
Low	ANT to RF1 On
High	ANT to RF2 On

Electrical Characteristics

Table 3 Absolute Maximum Ratings

Parameter	Symbol	Min	Max	Unit	Condition
DC Supply Voltage	V _{DD}	-0.3	3.3	V	T _A =25°C
Logic Control Voltage	V _{CTL}	-0.3	3.3		T _A =25°C
Max RF Input Power (ANT to RF1/RF2)	P _{IN}		36	dBm	F ₀ =950MHz, 20% DC, V _{DD} =2.8V, V _{CH} =1.8V, Z _O =50Ω, T _A =25°C
Device Operating Temperature	T _{OP}	-40	90		°C
Device Storage Temperature	T _{STG}	-55	150		
Electrostatic Discharge (All Pins)	V _{ESD(HBM)}	1000		V	Human Body Model
	V _{ESD(CDM)}	500			Charged Device Model

Notice

Exposure to maximum rating conditions for extended periods may reduce device reliability. There is no damage to device with only one parameter set at the limit and all other parameters set at or below their nominal value. Exceeding any of the limits listed here may result in permanent damage to the device.

Table 4 Recommended Operating Conditions

Parameter	Symbol	MIN	TYP	MAX	Unit
Operating Frequency	F ₀	0.4	-	3.0	GHz
DC Supply Voltage	V _{DD}	2.5	2.8	3.0	V
Control Voltage High	V _{CTL_H}	1.5	1.8	3.0	V
Control Voltage Low	V _{CTL_L}	0	0	0.3	V

Table 5 Nominal Operating Parameters

Parameter	Symbol	Specification			Unit	Condition	
		MIN	TYP	MAX			
Normal Conditions	V _{DD} =2.8V, V _{CTL_H} =1.8V, V _{CTL_L} =0V, P _{IN} =0dBm, Z ₀ =50Ω, T _A =25°C, Unless Otherwise Stated						
DC Performances							
DC Supply Current	I _{DD}		83	90	μA		
Current on VCTL	I _{CTL}			5			
Timing Performances							
Switching Speed	T _{SW}		1	2	μs	50% of VCTL to 10%/90% of RF	
Turn On Time	T _{ON}			10	μs	50% of VDD to 90% of RF	
RF Performances							
Insertion Loss (ANT to RF1/RF2)	IL		0.31 0.34 0.35	0.35 0.40 0.50	dB	F ₀ =0.4 to 1.0GHz F ₀ =1.7 to 2.1GHz F ₀ =2.2 to 3.0GHz	
Isolation (ANT to RF1/RF2)	ISO	35 28 23	40 30 25			dB	F ₀ =0.4 to 1.0GHz F ₀ =1.7 to 2.1GHz F ₀ =2.2 to 3.0GHz
Voltage Standing Wave Ratio(All Ports)	VSWR		1.25:1	1.50:1			F ₀ =0.4 to 3.0GHz
Input 0.1dB Compression Point (ANT to RF1/RF2)	P _{0.1dB}		35		dBm		F ₀ =950MHz, 20% DC
2nd Order Harmonic (ANT to RF1/RF2)	2F ₀		-100	-94	dBc	F ₀ =0.4 to 3.0GHz @26dBm	
3rd Order Harmonic (ANT to RF1/RF2)	3F ₀		-100	-95			

Package Outline Dimensions

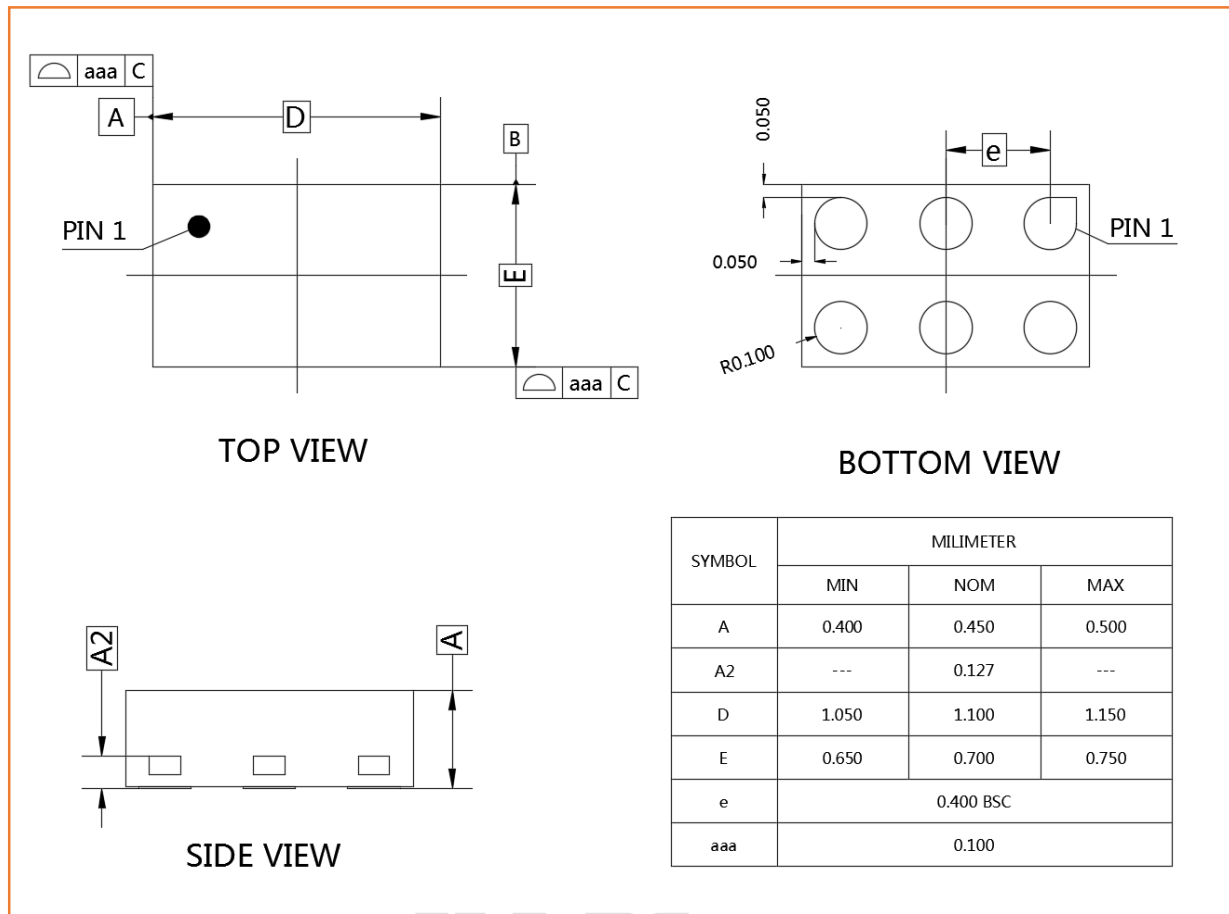


Figure 3 Package Outline Dimensions

Marking Specifications

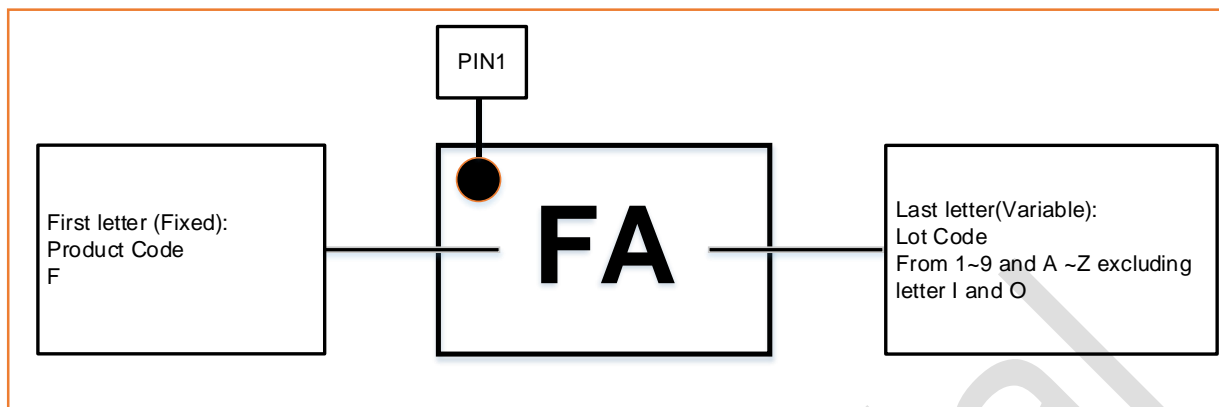


Figure 4 Marking Specifications (Top View)

Tape and Reel Dimensions

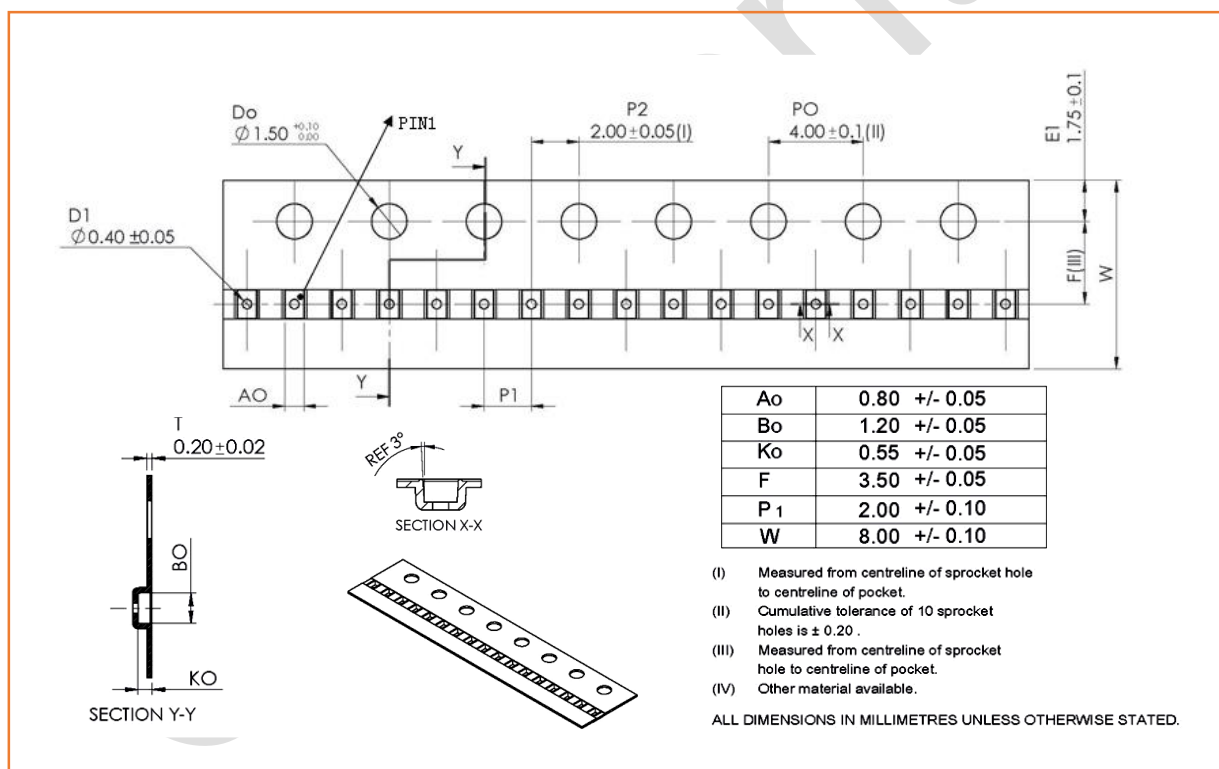


Figure 5 Tape and Reel Dimensions

Reflow Chart

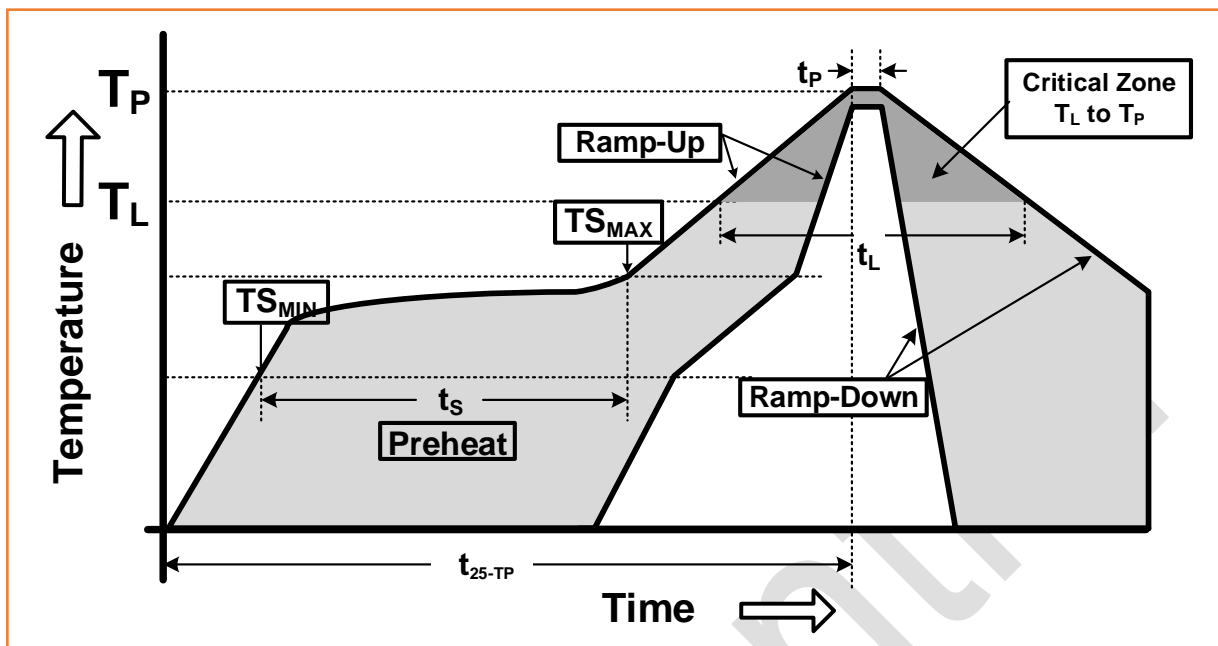


Figure 6 Recommended Lead-Free Reflow Profile

Table 6 Reflow Chart Parameters

Reflow Profile	Parameter
Preheat Temperature (TS _{MIN} to TS _{MAX})	150°C to 200°C
Preheat Time (t _s)	60 to 180 Seconds
Ramp-Up Rate (TS _{MAX} to T _P)	3°C/s MAX
Time Above T _L 217°C (t _L)	60 to 150 Seconds
Peak Temperature (T _P)	260°C
Time within 5°C of Peak Temperature (t _P)	20 to 40 Seconds
Ramp-Down Rate (TS _{MAX} to T _P)	6°C/s MAX
Time for 25°C to Peak Temperature (t _{25-TP})	8 Minutes MAX

ESD Sensitivity

Integrated circuits are ESD sensitive and can be damaged by static electric charge. Proper ESD protection techniques should be applied when devices are operated.

RoHS Compliant

This product does not contain lead, mercury, cadmium, hexavalent chromium, polybrominated biphenyls (PBB) and polybrominated diphenyl ethers (PBDE), and are considered RoHS compliant.